

ECE 3150 Homework #6 Solutions
(Farhan Rana)

6.1

a) $R_{min} = 0$ (trivial)

$$\text{In saturation: } \frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n V_{OUT}) = \frac{V_{DD} - V_{OUT}}{R}$$

$$\text{And: } V_{DS} \geq V_{GS} - V_{TN} \Rightarrow V_{OUT} \geq V_{IN} - V_{TN}$$

The former gives:

$$R = \frac{V_{DD} - V_{OUT}}{\frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n V_{OUT})}$$

Combined with $V_{OUT} \geq V_{IN} - V_{TN}$ gives.

$$R \leq R_{max} = \frac{V_{DD} - (V_{IN} - V_{TN})}{\frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n (V_{IN} - V_{TN}))}$$

See the plot on attached page.

$$b) I_D = 200 \mu A = \frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n V_{OUT})$$

$$V_{OUT} = 1.5V \Rightarrow V_{IN} = 0.917V$$

$$\text{Also, } R = \frac{V_{DD} - V_{OUT}}{I_D} = \frac{2.5 - 1.5}{200 \mu A} = 5k\Omega$$

d) As V_{IN} is increased, V_{OUT} decreases. When $V_{OUT} < V_{IN} - V_{TN}$ the FET goes out of saturation. At the boundary b/w saturation and linear region $V_{OUT} = V_{IN} - V_{TN}$

$$\Rightarrow \frac{W}{2L} \mu_n C_{ox} (V_{OUT})^2 (1 + \lambda_n V_{OUT}) = \frac{V_{DD} - V_{OUT}}{R} \quad \{ R = 5k\Omega \}$$

$$\Rightarrow V_{OUT} = 0.599V \Rightarrow V_{IN} = 0.599 + V_{TN} = 1.099V$$

on the other hand, as V_{IN} is decreased, V_{OUT} increases.

when $V_{IN} < V_{TN}$, FET goes into cut-off and $V_{OUT} = V_{DD} = 2.5V$.

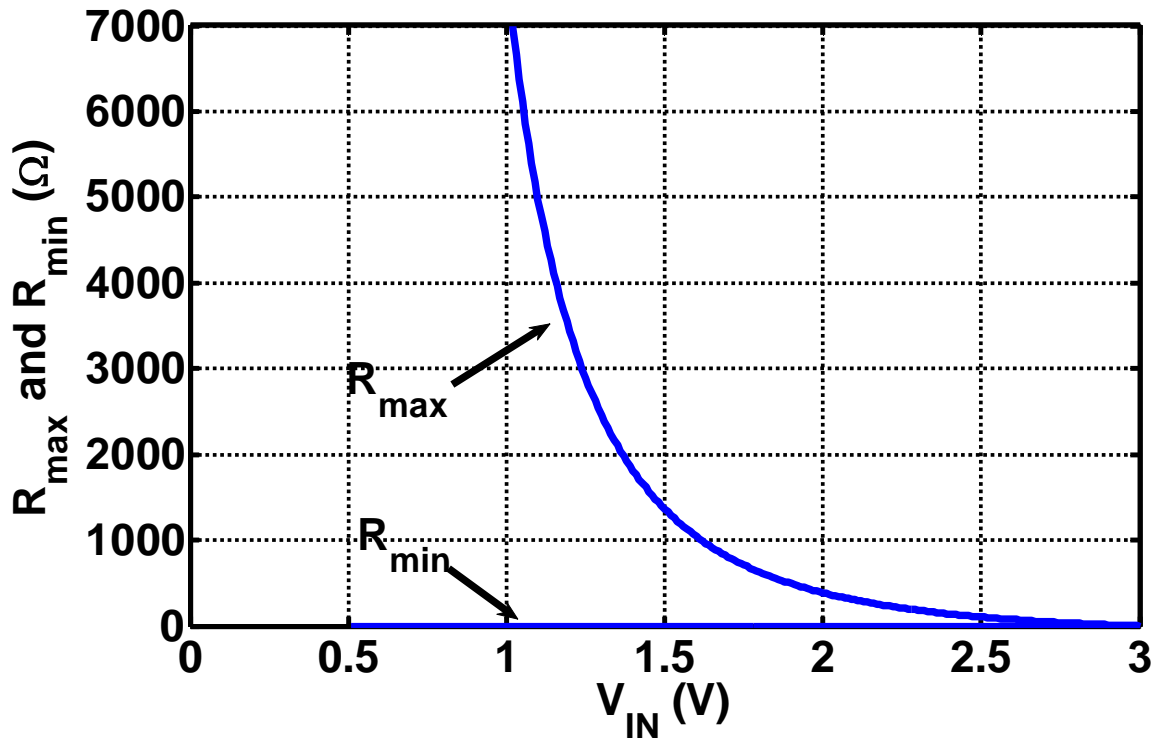
So for the FET to be in saturation:

$$0.599 < V_{OUT} < 2.5 \quad \text{Volts}$$

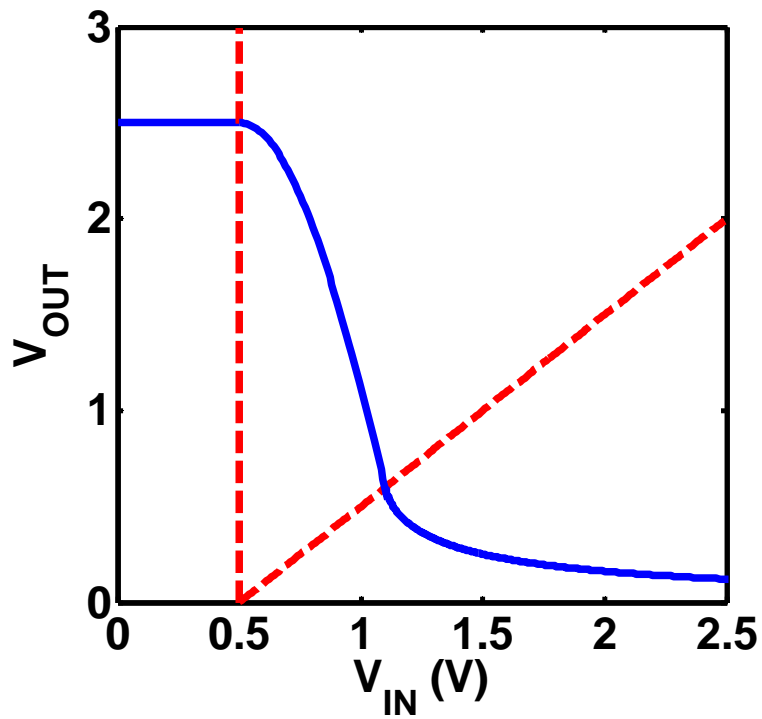
$$\& \quad V_{TN} < V_{IN} < 1.099 \quad \text{Volts.}$$

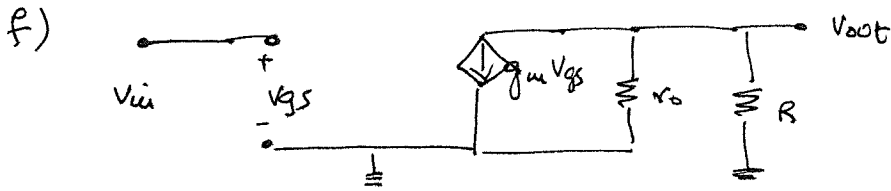
e) See attached plot.

Part (a)



Part (c)





$$A_v = \frac{V_{out}}{V_{in}} = -g_m (r_o \parallel R)$$

$$g_m = \frac{W}{L} \mu_n C_{ox} (V_{IN} - V_{TN}) (1 + \lambda_n V_{OUT}) = 9.59 \times 10^{-4} \text{ } \Omega^{-1}$$

$$g_o = \frac{1}{r_o} = \frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 \lambda_n = 1.739 \times 10^{-5} \text{ } \Omega^{-1}$$

$$\Rightarrow A_v = -4.41$$

g) Now we have:

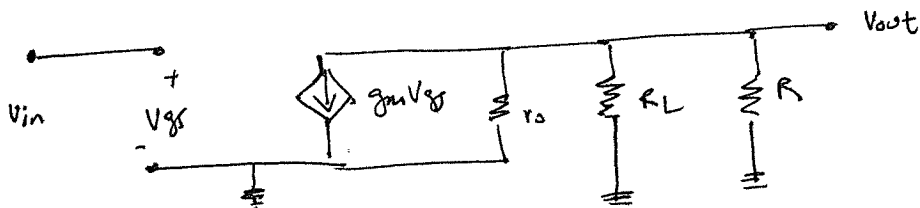
$$\frac{W}{2L} \mu_n C_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n V_{OUT}) = \frac{V_{DD} - V_{OUT}}{R} - \frac{V_{OUT}}{R_L}$$

$$\Rightarrow V_{OUT} = 1.028 \text{ Volt} \quad I_{OUT} = 102.75 \text{ } \mu\text{A}$$

b) Now $g_m = 9.19 \times 10^{-4} \text{ } \Omega^{-1}$

$$g_o = \frac{1}{r_o} = 1.739 \times 10^{-5} \text{ } \Omega^{-1}$$

$$A_v = -g_m (r_o \parallel R \parallel R_L) = -2.895$$



6.2.

a) Suppose both FETs are in saturation. Then

$$\frac{W}{2L} \mu_n \epsilon_{ox} (V_{IN} - V_{TN})^2 (1 + \lambda_n V_{OUT}) = \frac{W}{2L} \mu_n \epsilon_{ox} (V_{DD} - V_{OUT} - V_{TN})^2 (1 + \lambda_n (V_{DD} - V_{OUT}))$$

$$\Rightarrow (0.75)^2 (1 + 0.1 V_{OUT}) = (2 - V_{OUT})^2 (1 + 0.1 (2.5 - V_{OUT}))$$

$\Rightarrow V_{OUT} = 1.25 \text{ V}$ \Rightarrow For this V_{OUT} bottom FET is in saturation.
And the top FET is always in saturation (or cut-off)

b) Again suppose both FETs are in saturation. Use eq. from part (a):

$$\Rightarrow (1.5)^2 (1 + 0.1 V_{OUT}) = (2 - V_{OUT})^2 (1 + 0.1 (2.5 - V_{OUT}))$$

$$\Rightarrow V_{OUT} = 0.586 \text{ V}$$

BUT now $V_{OUT} < V_{IN} - V_{TN} = 1.5 \text{ V}$ \Rightarrow bottom FET must be in linear or triode region. So we have (now):

$$\frac{W}{L} \mu_n \epsilon_{ox} \left(V_{IN} - V_{TN} - \frac{V_{OUT}}{2} \right) V_{OUT} (1 + \lambda_n V_{OUT}) = \frac{W}{2L} \mu_n \epsilon_{ox} (V_{DD} - V_{OUT} - V_{TN})^2 (1 + \lambda_n (V_{DD} - V_{OUT}))$$

$$\Rightarrow (1.5 - \frac{V_{OUT}}{2}) V_{OUT} (1 + 0.1 V_{OUT}) = 0.5 (2 - V_{OUT})^2 (1 + 0.1 (2.5 - V_{OUT}))$$

$$\Rightarrow V_{OUT} = 0.755 \text{ V} \quad \Rightarrow \text{bottom FET is in linear region.}$$

c) If $V_{OUT} \geq 2.0 \text{ V}$, the top FET will go into cut-off.

So V_{OUT} needs to be less than 2.0 Volts.

V_{IN} can be found from the eq. in part (a): $V_{IN} = 0.5 \text{ Volts}$.

So if $V_{IN} > 0.5 \text{ Volts}$, $V_{OUT} < 2.0 \text{ Volts}$ and none of the FETs will be in cut-off.

d) If V_{IN} is too large, V_{OUT} will be so small that the bottom

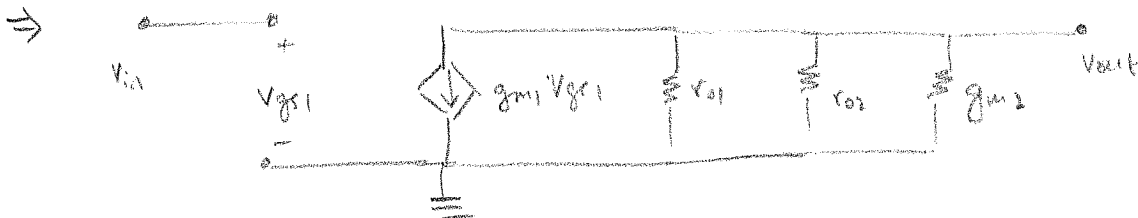
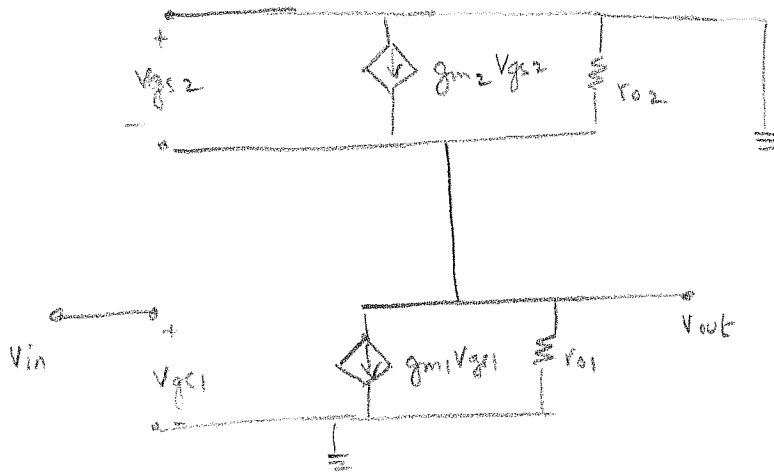
FET will go into the linear region (as was the case in part (b)).

At the boundary b/w linear and saturation region $V_{out} = V_{in} - V_{TN}$.

$$\Rightarrow \frac{W}{2L} \mu_n C_{ox} (V_{out})^2 (1 + \lambda_n V_{out}) = \frac{W}{2L} \mu_n C_{ox} (V_{DD} - V_{out} - V_{TN})^2 (1 + \lambda_n (V_{DD} - V_{out}))$$

$$\Rightarrow V_{out} = 1.01 \text{ Volt} \quad \text{and} \quad V_{in} = 1.51 \text{ Volt}$$

c)



$$A_v = -g_{m1} \left(r_{o1} \parallel r_{o2} \parallel \frac{1}{g_{m2}} \right) \quad \left\{ \begin{array}{l} \text{since } r_{o1} \sim r_{o2} \gg \frac{1}{g_{m2}} \\ A_v \sim -\frac{g_{m1}}{g_{m2}} \sim -1 \rightarrow \text{rough estimate} \end{array} \right.$$

$$f) V_{in} = 1.25 \text{ V} \Rightarrow g_{m1} = g_{m2} = \frac{W}{L} \mu_n C_{ox} (0.75) (1 + 0.1 \times 1.25) = 1.7 \times 10^{-3} \Omega^{-1}$$

$$g_{o1} = g_{o2} = r_{o1}^{-1} = r_{o2}^{-1} = \frac{W}{2L} \mu_n C_{ox} (0.75)^2 \cdot 0.1 = 5.63 \times 10^{-5} \Omega^{-1}$$

$$\Rightarrow A_v = -0.9379$$

6.3

a) Just by the symmetry of PFET and NFET ($k_n = k_p$) one can guess that $V_{out} = 1.25$ V and both FETs are in saturation.

b) If V_{out} becomes too large the PFET will go into the linear region. This would happen when $V_{out} - V_{DD} > V_B - V_{DD} - V_{TP}$

$$\Rightarrow V_{out} > +1.75 \text{ Volts}$$

When the PFET is at the boundary b/w linear and saturation regions $V_{out} = 1.75$ Volts.

$$\Rightarrow \frac{k_n}{2} (V_{in} - V_{TN})^2 (1 + \lambda_n V_{out}) = \frac{k_p}{2} (V_B - V_{DD} - V_{TP})^2 (1 - 0.1(V_{out} - V_{DD}))$$

$$\Rightarrow V_{in} = 1.218 \text{ Volts}$$

c) If V_{out} becomes too small, NFET will go into the linear region. This would happen when $V_{out} = V_{in} - V_{TN}$

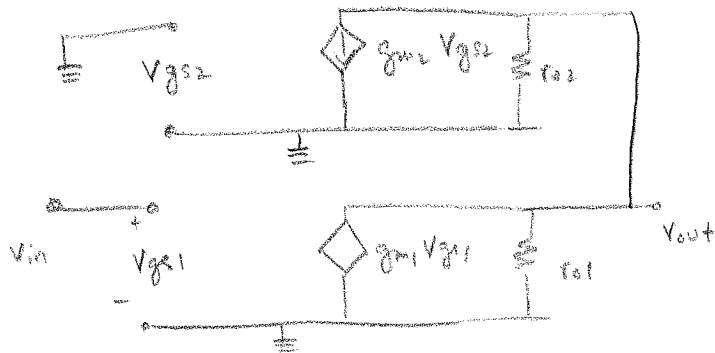
$$\Rightarrow \frac{k_n}{2} (V_{out})^2 (1 + \lambda_n V_{out}) = \frac{k_p}{2} (V_B - V_{DD} - V_{TP})^2 (1 - 0.1(V_{out} - V_{DD}))$$

$$\Rightarrow V_{out} = 0.782 \text{ Volts}$$

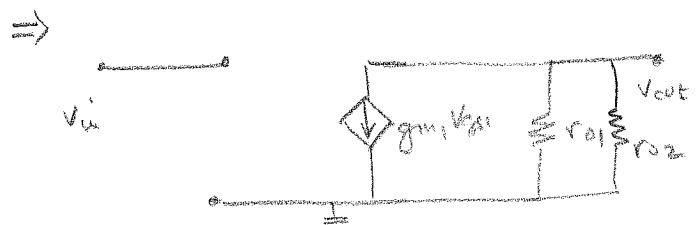
$$\Rightarrow V_{in} = 1.282 \text{ Volts}$$

b) + c) \Rightarrow Output Voltage swing: $0.782 < V_{out} < 1.75$
 Input Voltage swing: $1.218 < V_{in} < 1.282$

d)



$$A_v = -g_{m1} (r_{ds1} \parallel r_{ds2})$$



$$e) \quad g_{m1} = g_{m2} = \kappa_n (V_{IN} - V_{TN}) (1 + \lambda_n V_{DS1T}) = 1.7 \times 10^{-3} \text{ } \Omega^{-1}$$

$$r_{o1}^{-1} = r_{o2}^{-1} = \frac{\kappa_n}{2} (V_{IN} - V_{TN})^2 \lambda_n = 5.63 \times 10^{-5} \text{ } \Omega^{-1}$$

$$AV = -15 \quad (\text{pretty large!})$$

f) 6.1(f) the gain A_v was modest (-2.895)

6.2(f) the gain was less than unity (-0.9979)

So 6.3(e) wins in terms of the gain!